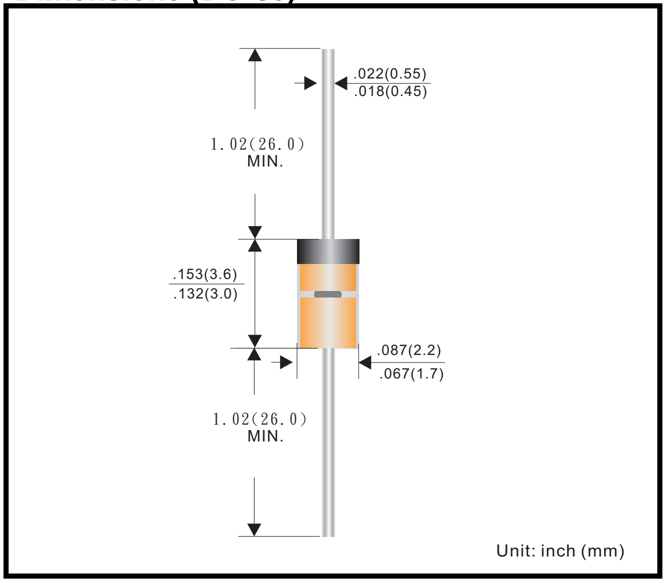
1N914B SIGNAL DIODE

Pb Free Product

Absolute Maximum Ratings (Ta=25°C)

Items	Symbol	Ratings	Unit
Reverse Voltage	VR	75	V
Reverse Recovery Time	trr	4	ns
Power Dissipation 3.33mW/°C (25°C)	P	500	mW
Forward Current	IF	300	mA
Junction Temp.	Tj	-65 to 175	°C
Storage Temp.	Tstg	-65 to 175	°C

Dimensions (DO-35)



Mechanical Data

Items	Materials
Package	DO-35
Case	Hermetically sealed glass
Lead/Finish	Double stud/Solder Plating
Chip	Glass Passivated

Electrical Characteristics (Ta=25°C)

Ratings	Symbol	Ratings	Unit
Minimum Breakdown Voltage	BV		V
IR= 5.0uA		75	
IR= 100uA		100	
Peak Forward Surge Current PW= 1sec.	IFsurge	0.5	A
Maximum Forward Voltage	VF		V
IF= 100mA		1.0	
Maximum Reverse Current	IR		uA
VR= 20V		0.025	
VR= 75V		5.0	
VR= 20V, Tj= 150°C		50	
Maximum Junction Capacitance	Cj		pF
VR= 0, f= 1 MHz		4	
Maximum Reverse Recovery Time	trr		ns
IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω		4	

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

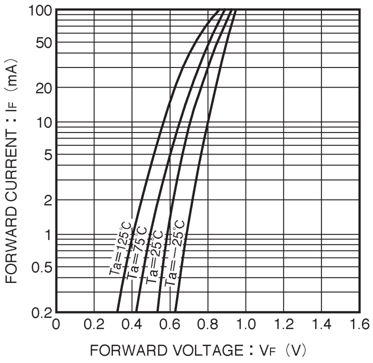


Fig. 1 Forward characteristics

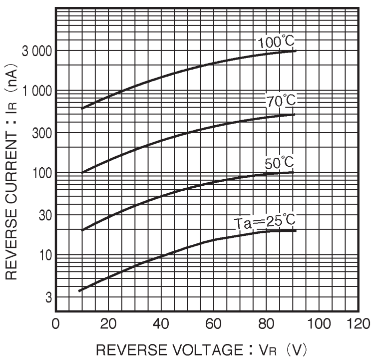


Fig. 2 Reverse characteristics

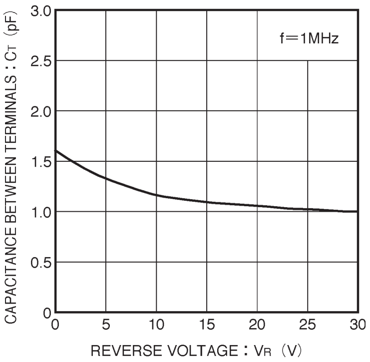


Fig. 3 Capacitance between terminals characteristics

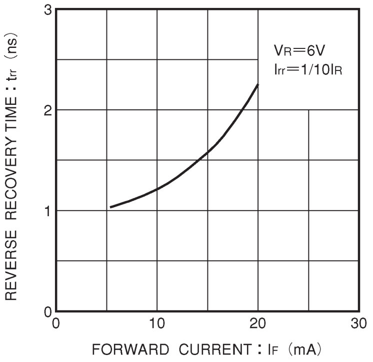


Fig. 4 Reverse recovery time characteristics

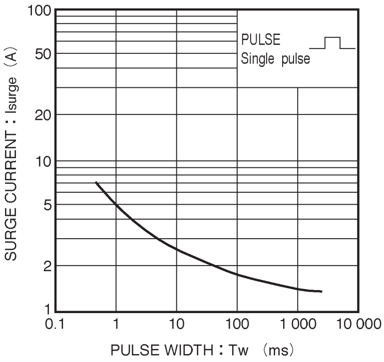


Fig. 5 Surge current characteristics

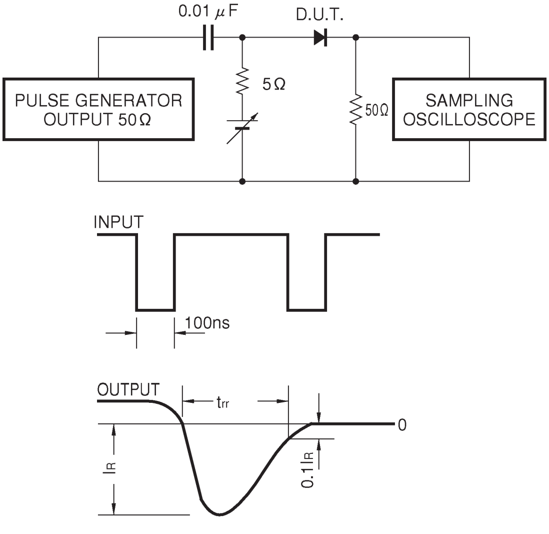


Fig. 6 Reverse recovery time (trr) measurement circuit